

# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



# BT138-600

4Q Triac

29 August 2013

Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

## 2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

## 4. Quick reference data

Table 1. Quick reference data

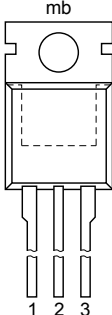
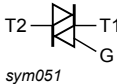
| Symbol                        | Parameter                            | Conditions                                                                                                                                                 | Min | Typ | Max | Unit               |
|-------------------------------|--------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|--------------------|
| $V_{\text{DRM}}$              | repetitive peak off-state voltage    |                                                                                                                                                            | -   | -   | 600 | V                  |
| $I_{\text{TSM}}$              | non-repetitive peak on-state current | full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 95  | A                  |
| $T_{\text{J}}$                | junction temperature                 |                                                                                                                                                            | -   | -   | 125 | $^{\circ}\text{C}$ |
| $I_{\text{T(RMS)}}$           | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 99\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                 | -   | -   | 12  | A                  |
| <b>Static characteristics</b> |                                      |                                                                                                                                                            |     |     |     |                    |
| $I_{\text{GT}}$               | gate trigger current                 | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | -   | 5   | 35  | mA                 |
|                               |                                      | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | -   | 8   | 35  | mA                 |
|                               |                                      | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2- G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | -   | 10  | 35  | mA                 |



| Symbol                         | Parameter                         | Conditions                                                                                                                              | Min | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------------------|
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -   | 22  | 70  | mA               |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                         |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 100 | 250 | -   | V/ $\mu\text{s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline                                                                                         | Graphic symbol                                                                      |
|-----|--------|--------------------------------|------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | T1     | main terminal 1                |  <p>TO-220AB (SOT78)</p> |  |
| 2   | T2     | main terminal 2                |                                                                                                            |                                                                                     |
| 3   | G      | gate                           |                                                                                                            |                                                                                     |
| mb  | T2     | mounting base; main terminal 2 |                                                                                                            |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package  |                                                                                  |         |
|--------------|----------|----------------------------------------------------------------------------------|---------|
|              | Name     | Description                                                                      | Version |
| BT138-600    | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |
| BT138-600/DG | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

## 7. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions                                                                                                                                          |  | Min | Max | Unit                   |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                                     |  | -   | 600 | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 99\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>          |  | -   | 12  | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> |  | -   | 95  | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$                                                 |  | -   | 105 | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; sine-wave pulse                                                                                                     |  | -   | 45  | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 20\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+                               |  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 20\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-                               |  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 20\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-                               |  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 20\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+                               |  | -   | 10  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |                                                                                                                                                     |  | -   | 2   | A                      |
| $P_{\text{GM}}$     | peak gate power                      |                                                                                                                                                     |  | -   | 5   | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period                                                                                                                               |  | -   | 0.5 | W                      |
| $T_{\text{stg}}$    | storage temperature                  |                                                                                                                                                     |  | -40 | 150 | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |                                                                                                                                                     |  | -   | 125 | $^{\circ}\text{C}$     |

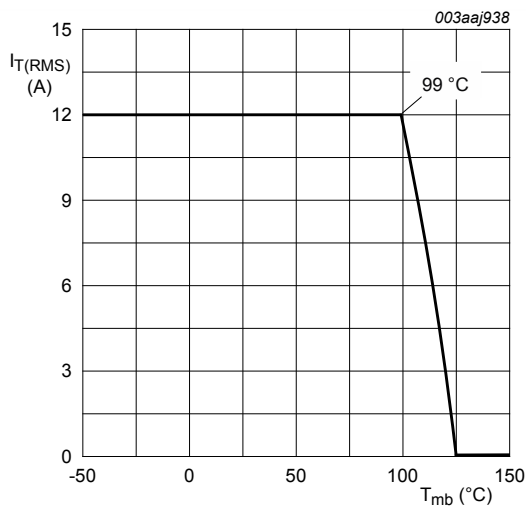
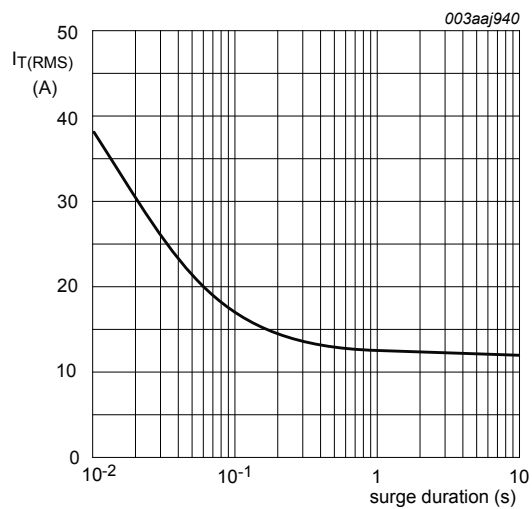


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz;  $T_{mb}$  = 99 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

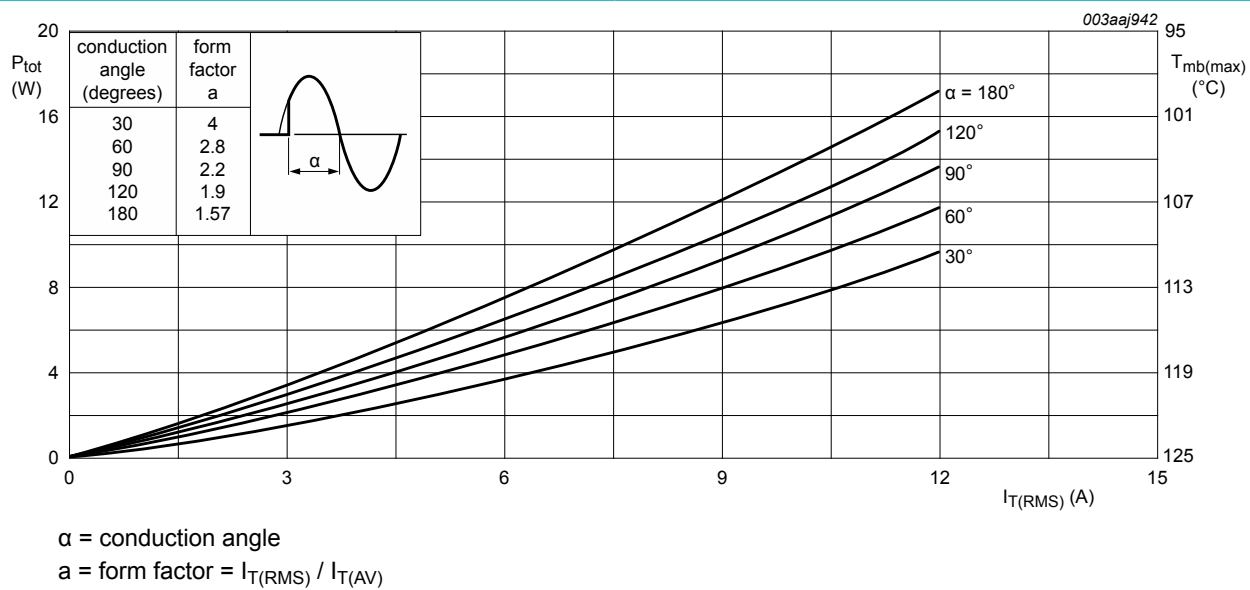
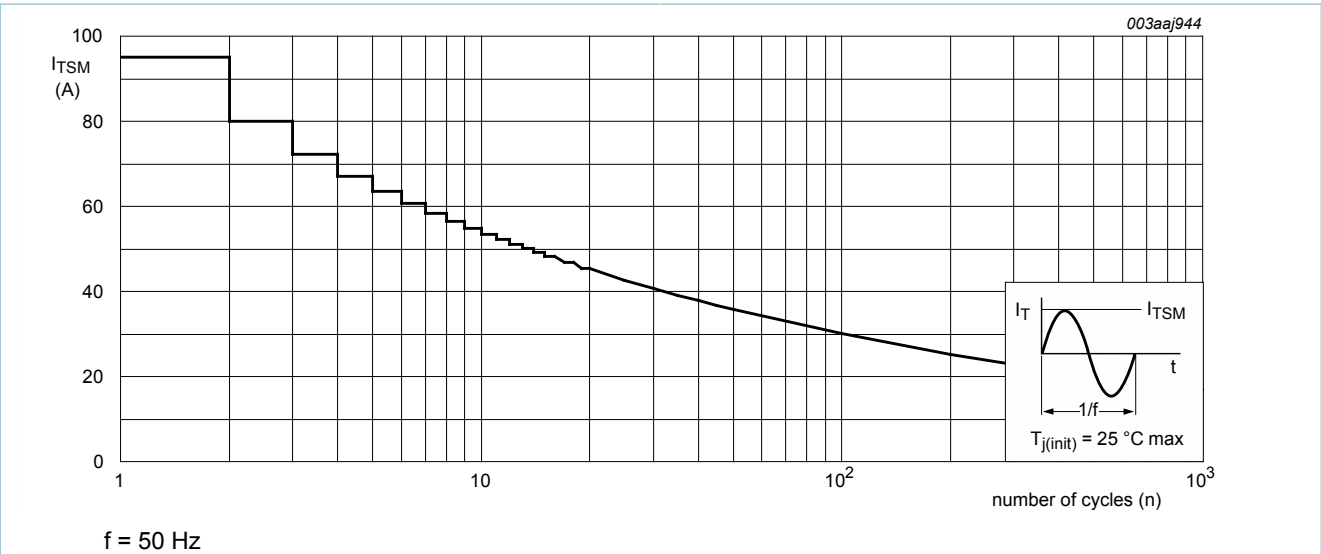
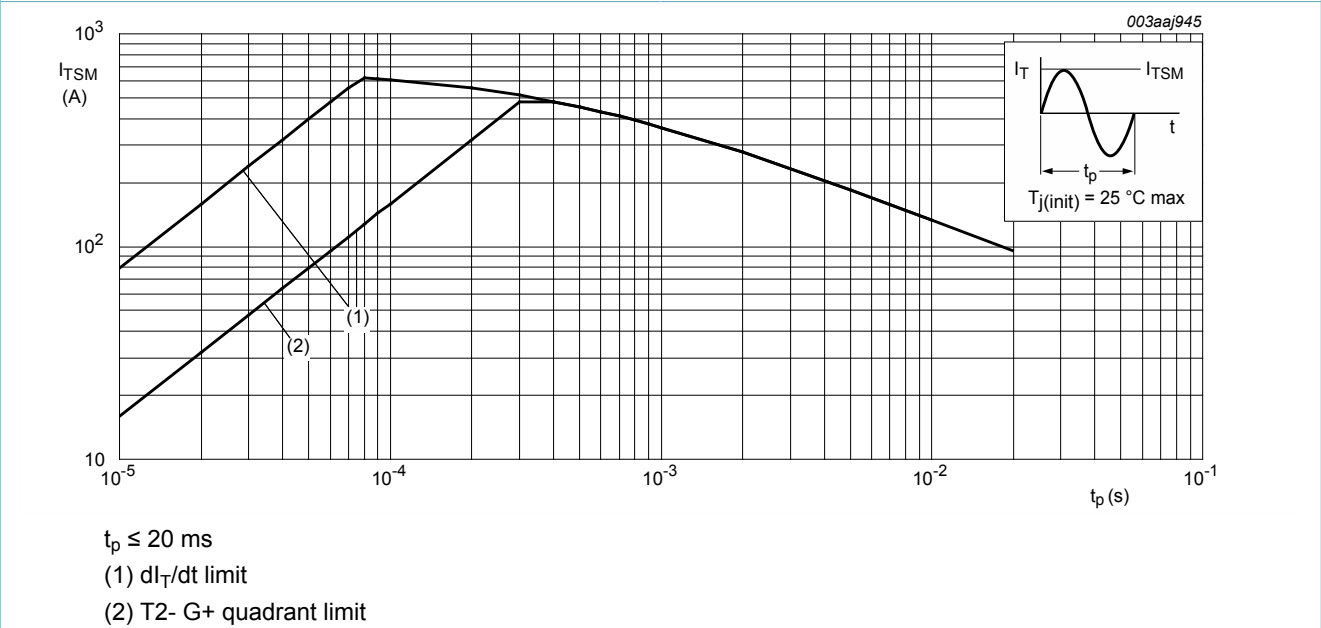


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4.** Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

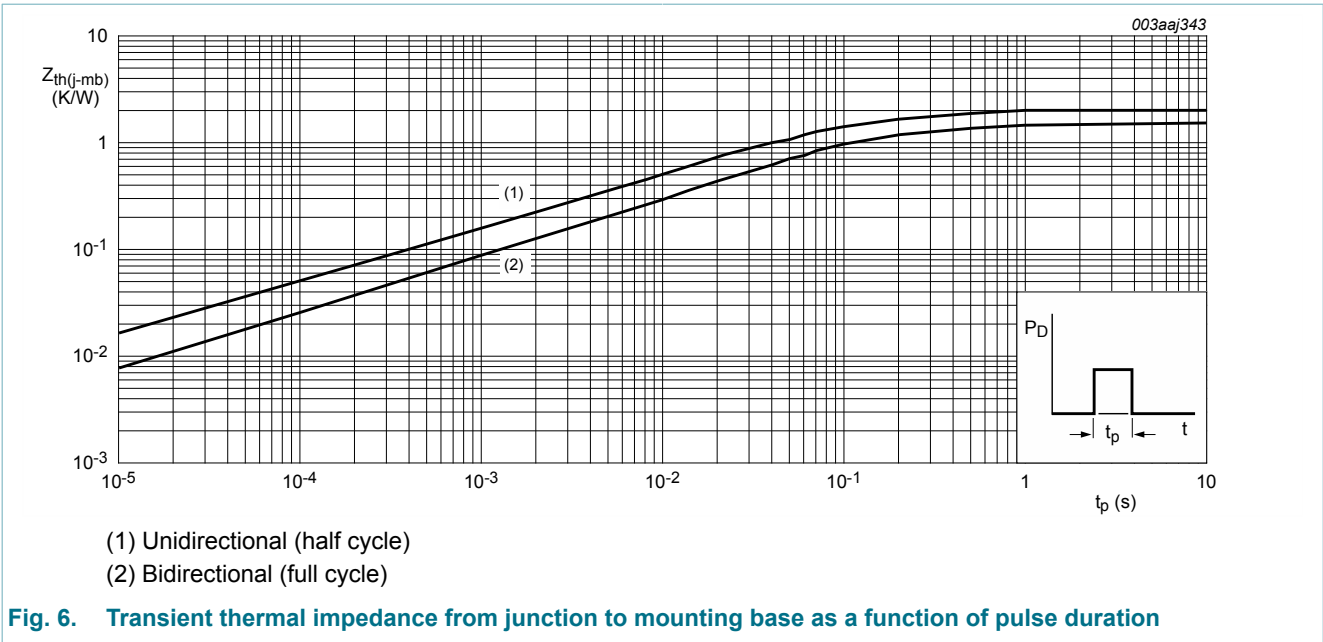


**Fig. 5.** Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions         | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|--------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | -   | -   | 1.5 | K/W  |
|                |                                                   | half cycle; Fig. 6 | -   | -   | 2   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air        | -   | 60  | -   | K/W  |

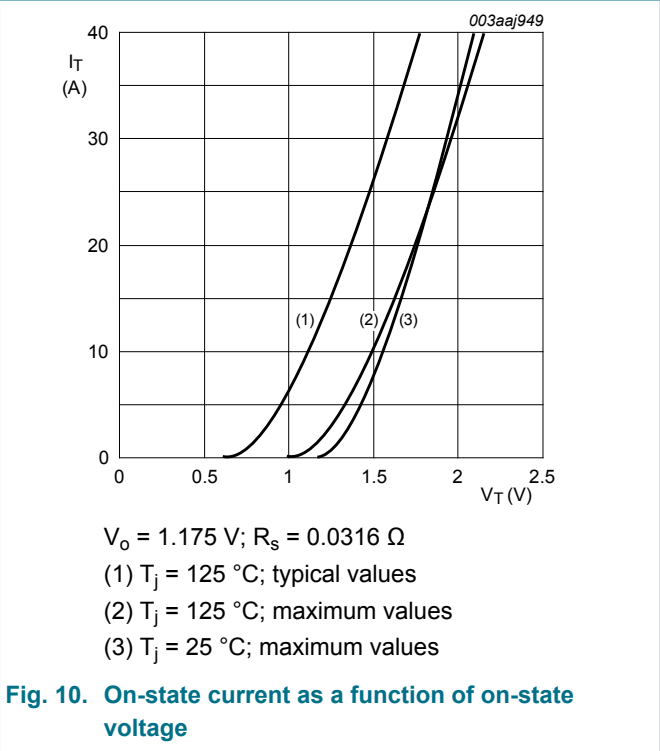
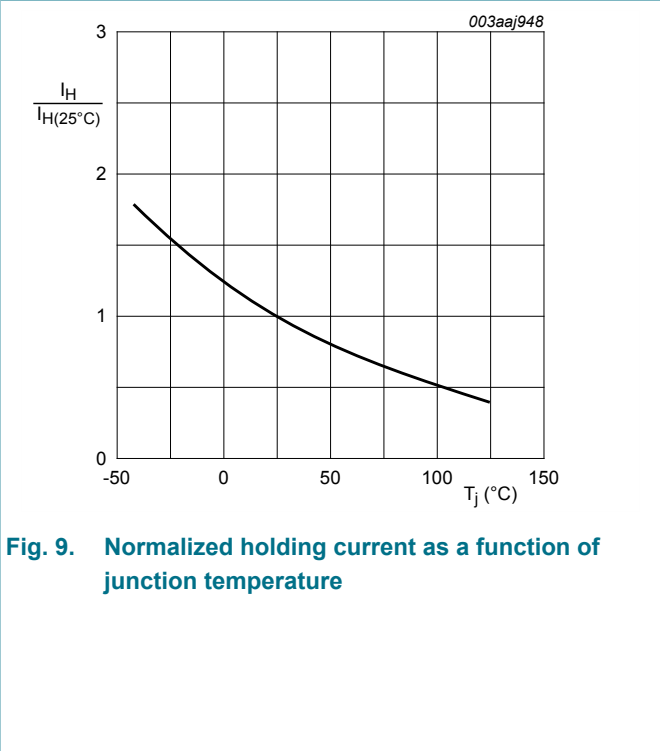
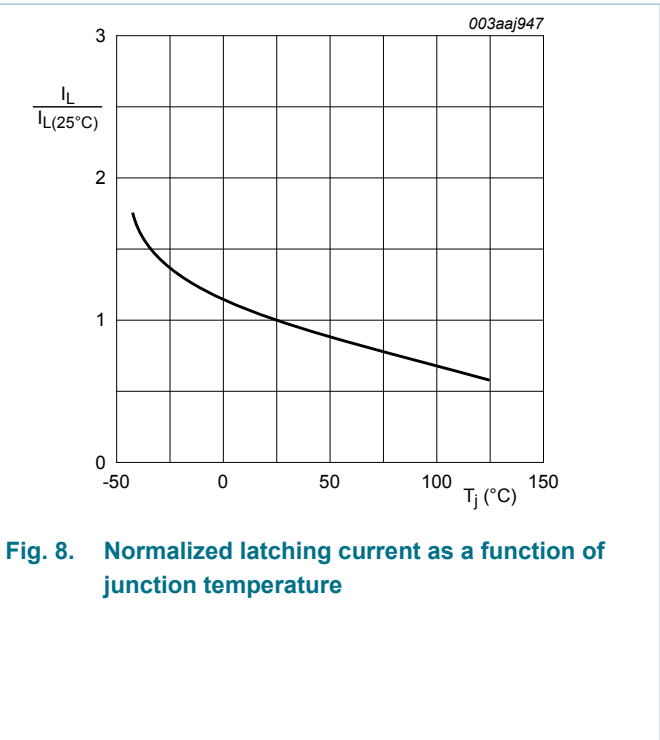
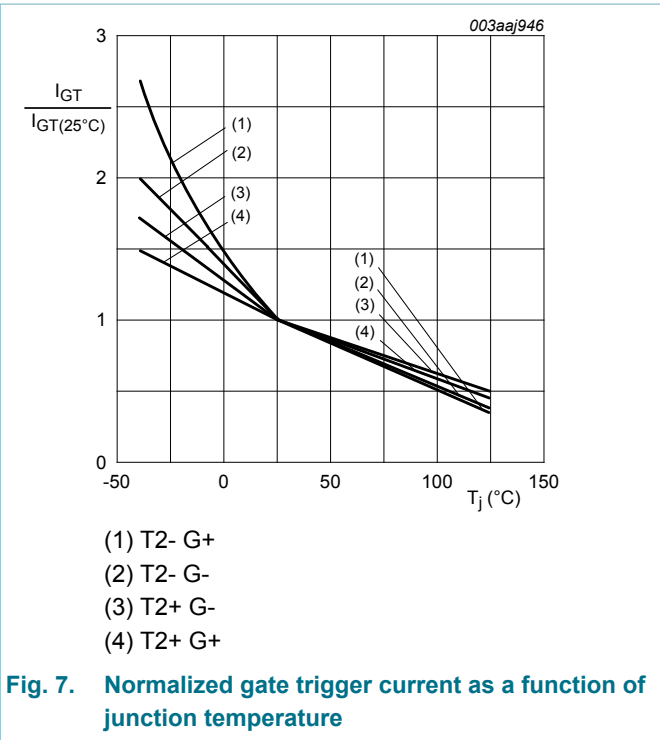


## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                         | Conditions                                                                                                                              |  | Min  | Typ | Max  | Unit             |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|--|------|-----|------|------------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                         |  |      |     |      |                  |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       |  | -    | 5   | 35   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       |  | -    | 8   | 35   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       |  | -    | 10  | 35   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       |  | -    | 22  | 70   | mA               |
| $I_L$                          | latching current                  | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       |  | -    | 7   | 40   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       |  | -    | 20  | 60   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       |  | -    | 8   | 40   | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       |  | -    | 10  | 60   | mA               |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                                         |  | -    | 6   | 30   | mA               |
| $V_T$                          | on-state voltage                  | $I_T = 15\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                        |  | -    | 1.4 | 1.65 | V                |
| $V_{GT}$                       | gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                              |  | -    | 0.7 | 1    | V                |
|                                |                                   | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                            |  | 0.25 | 0.4 | -    | V                |
| $I_D$                          | off-state current                 | $V_D = 600\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                |  | -    | 0.1 | 0.5  | mA               |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                         |  |      |     |      |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit |  | 100  | 250 | -    | V/ $\mu\text{s}$ |
| $t_{gt}$                       | gate-controlled turn-on time      | $I_{TM} = 16\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$                               |  | -    | 2   | -    | $\mu\text{s}$    |





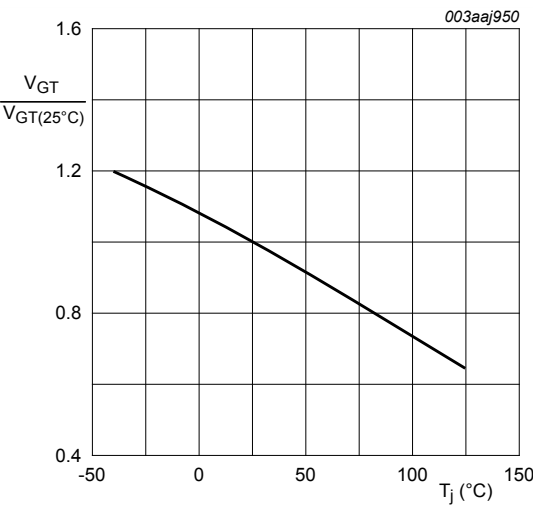


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

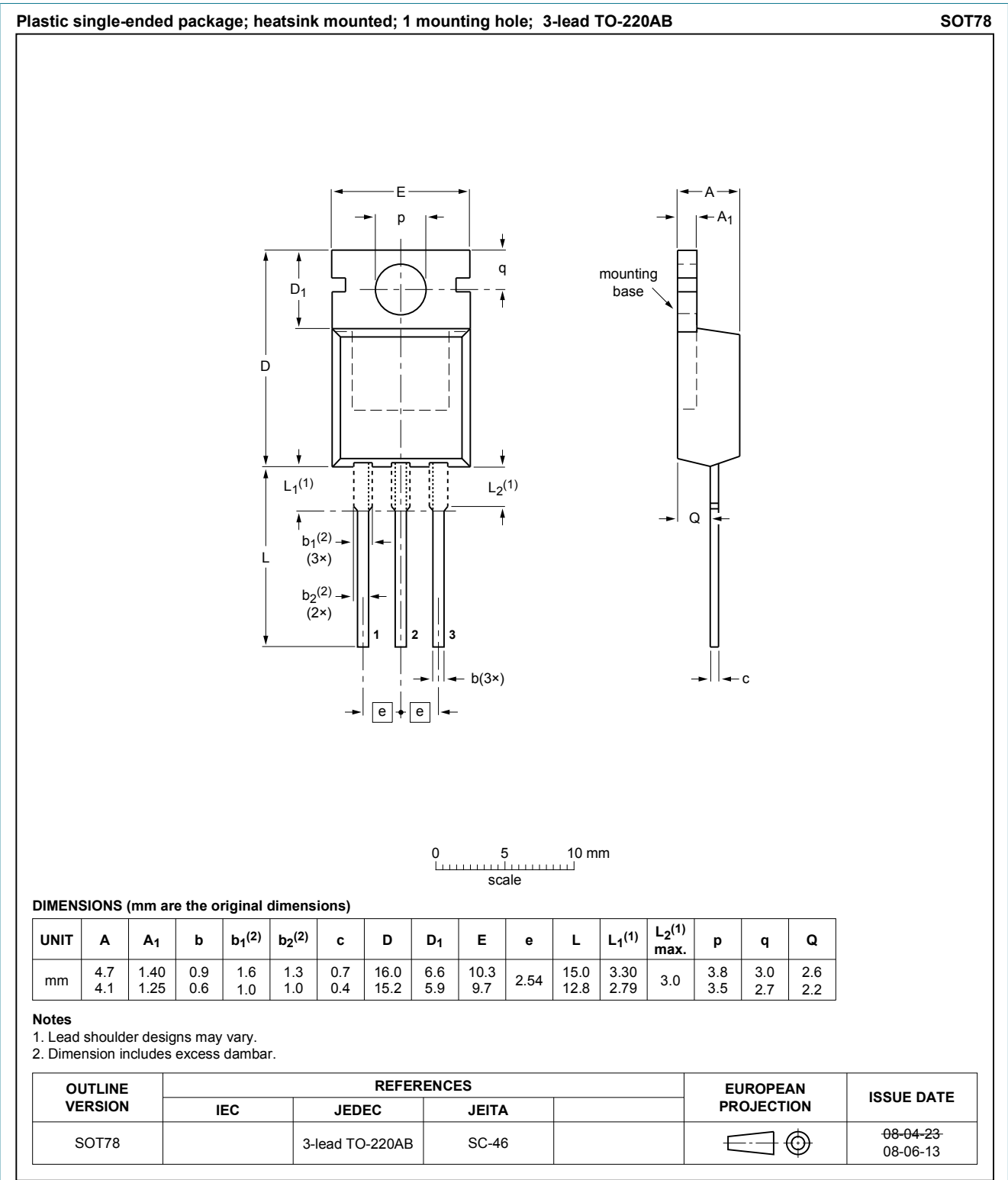


Fig. 12. Package outline TO-220AB (SOT78)

## 11. Legal information

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| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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12. Contents

1 General description ..... 1

2 Features and benefits ..... 1

3 Applications ..... 1

4 Quick reference data ..... 1

5 Pinning information ..... 2

6 Ordering information ..... 2

7 Limiting values ..... 3

8 Thermal characteristics ..... 6

9 Characteristics ..... 7

10 Package outline ..... 10

11 Legal information ..... 11

11.1 Data sheet status ..... 11

11.2 Definitions ..... 11

11.3 Disclaimers ..... 11

11.4 Trademarks ..... 12

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